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ISSUE DATE

U.S. UTILITY Patent Application

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**APPLICANTS: Hayashi Nobuhiko; Kunisato Tatsuya; Ohbo Hiroki; Yamaguchi Tsutomu; <div style="text-align: right;">3818</div>					
**CONTINUING DATA VERIFIED: <u>None</u>					
** FOREIGN APPLICATIONS VERIFIED: <u>462</u> JAPAN JF2001-56284 03/01/2001					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		<input checked="" type="checkbox"/> RESCIND <input type="checkbox"/>			
Foreign priority claimed 35 USC 119 (continuous) and Modified and 44 USC 2402 (non-continuous) Initials T. L. : Hayashi Nobuhiko et al. semiconductor element and method of forming nitride-based semiconductor		5 year Q no 5 year Q no 57810-033		ATTORNEY DOCKET NO 57810-033	
<small>U.S. DEPT. OF COMMERCE PAT & TM # 910-436 (Rev. 12-94)</small>					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	Total Claims Print Claims for O.G.
ISSUE FEE		Primary Examiner	DRAWING
Amount Due	Date Paid		Sheets Drawn Figs. Drawn Print Figs.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE Application Examiner	
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